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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	280
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe1500-2fgg484i

SRAM and FIFO

ProASIC3E devices have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro.

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

ProASIC3E devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC3E family contains six CCCs, each with an integrated PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides.

To maximize user I/Os, only the center east and west PLLs are available in devices using the PQ208 package. However, all six CCC blocks are still usable; the four corner CCCs allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz to 350 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from –7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration.
- Output duty cycle = 50% ± 1.5% or better
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used
- Maximum acquisition time = 300 µs
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter— allowable input jitter is up to 1.5 ns
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × (350 MHz / f_{OUT_CCC})

Global Clocking

ProASIC3E devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high fanout nets.

Table 2-2 • Recommended Operating Conditions [1]

Symbol	Parameter		Commercial	Industrial	Units
T_A	Ambient temperature		0 to +70	–40 to +85	°C
T_J	Junction temperature		0 to +85	–40 to +100	°C
VCC	1.5 V DC core supply voltage		1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode [2]	3.15 to 3.45	3.15 to 3.45	V
		Operation [3]	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV [4]	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.0 V DC supply voltage [5]		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. *All parameters representing voltages are measured with respect to GND unless otherwise specified.*
2. *The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.*
3. *VPUMP can be left floating during normal operation (not programming mode).*
4. *The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-13 on page 2-16. VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
5. *To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools.*
6. *3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.*

Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature [1]

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Table 2-4 • **Overshoot and Undershoot Limits** [1]

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at 85°C.*
2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*
3. *This table does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3E device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4.

There are five regions to consider during power-up.

ProASIC3E I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

Calculating Power Dissipation

Quiescent Supply Current

Table 2-7 • **Quiescent Supply Current Characteristics**

	A3PE600	A3PE1500	A3PE3000
Typical (25°C)	5 mA	12 mA	25 mA
Maximum (Commercial)	30 mA	70 mA	150 mA
Maximum (Industrial)	45 mA	105 mA	225 mA

Notes:

1. *IDD Includes VCC, VPUMP, VCCI, and VMV currents. Values do not include I/O static contribution, which is shown in Table 2-8 and Table 2-9 on page 2-7.*
2. *–F speed grade devices may experience higher standby IDD of up to five times the standard IDD and higher I/O leakage.*

Power per I/O Pin

Table 2-8 • **Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings**

	VMV (V)	Static Power PDC2 (mW)[1]	Dynamic Power PAC9 (µW/MHz)[2]
Single-Ended			
3.3 V LVTTL/LVCMOS	3.3	–	17.39
3.3 V LVTTL/LVCMOS – Schmitt trigger	3.3	–	25.51
3.3 V LVTTL/LVCMOS Wide Range[3]	3.3	–	16.34
3.3 V LVTTL/LVCMOS Wide Range – Schmitt trigger[3]	3.3	–	24.49
2.5 V LVCMOS	2.5	–	5.76
2.5 V LVCMOS – Schmitt trigger	2.5	–	7.16
1.8 V LVCMOS	1.8	–	2.72
1.8 V LVCMOS – Schmitt trigger	1.8	–	2.80
1.5 V LVCMOS (JESD8-11)	1.5	–	2.08
1.5 V LVCMOS (JESD8-11) – Schmitt trigger	1.5	–	2.00
3.3 V PCI	3.3	–	18.82
3.3 V PCI – Schmitt trigger	3.3	–	20.12
3.3 V PCI-X	3.3	–	18.82
3.3 V PCI-X – Schmitt trigger	3.3	–	20.12
Voltage-Referenced			
3.3 V GTL	3.3	2.90	8.23
2.5 V GTL	2.5	2.13	4.78
3.3 V GTL+	3.3	2.81	4.14
2.5 V GTL+	2.5	2.57	3.71

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.*

Table 2-17 • **Summary of I/O Timing Characteristics—Software Default Settings**
–2 Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength (mA)	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PYS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)
3.3 V LVTTL / 3.3 V LVCMOS	12	12	High	35	–	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	35	–	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79
2.5 V LVCMOS	12	12	High	35	–	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28
1.8 V LVCMOS	12	12	High	35	–	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98
1.5 V LVCMOS	12	12	High	35	–	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37
3.3 V PCI	Per PCI spec	–	High	10	25 [3]	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V PCI-X	Per PCI-X spec	–	High	10	25[3]	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V GTL	20 [4]	–	High	10	25	0.45	1.55	0.03	2.19	–	0.32	1.52	1.55	–	–	3.19	3.22
2.5 V GTL	20 [4]	–	High	10	25	0.45	1.59	0.03	1.83	–	0.32	1.61	1.59	–	–	3.28	3.26
3.3 V GTL+	35	–	High	10	25	0.45	1.53	0.03	1.19	–	0.32	1.56	1.53	–	–	3.23	3.20
2.5 V GTL+	33	–	High	10	25	0.45	1.65	0.03	1.13	–	0.32	1.68	1.57	–	–	3.35	3.24
HSTL (I)	8	–	High	20	50	0.49	2.37	0.03	1.59	–	0.32	2.42	2.35	–	–	4.09	4.02
HSTL (II)	15 [4]	–	High	20	25	0.49	2.26	0.03	1.59	–	0.32	2.30	2.03	–	–	3.97	3.70
SSTL2 (I)	15	–	High	30	50	0.49	1.59	0.03	1.00	–	0.32	1.62	1.38	–	–	3.29	3.05
SSTL2 (II)	18	–	High	30	25	0.49	1.62	0.03	1.00	–	0.32	1.65	1.32	–	–	3.32	2.99
SSTL3 (I)	14	–	High	30	50	0.49	1.72	0.03	0.93	–	0.32	1.75	1.37	–	–	3.42	3.04
SSTL3 (II)	21	–	High	30	25	0.49	1.54	0.03	0.93	–	0.32	1.57	1.25	–	–	3.24	2.92
LVDS/B-LVDS/ M-LVDS	24	–	High	–	–	0.49	1.40	0.03	1.36	–	–	–	–	–	–	–	–
LVPECL	24	–	High	–	–	0.49	1.36	0.03	1.22	–	–	–	–	–	–	–	–

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3V wide range as specified in the JESD8b specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-38 for connectivity. This resistor is not required during normal operation.*
4. *Output drive strength is below JEDEC specification.*
5. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5.*

Timing Characteristics

***Table 2-31* • 3.3 V LVCMOS Wide Range High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.66	12.19	0.04	1.83	2.38	0.43	12.19	10.17	4.16	4.00	15.58	13.57	ns
		–1	0.56	10.37	0.04	1.55	2.02	0.36	10.37	8.66	3.54	3.41	13.26	11.54	ns
		–2	0.49	9.10	0.03	1.36	1.78	0.32	9.10	7.60	3.11	2.99	11.64	10.13	ns
100 µA	8 mA	Std.	0.66	7.85	0.04	1.83	2.38	0.43	7.85	6.29	4.71	4.97	11.24	9.68	ns
		–1	0.56	6.68	0.04	1.55	2.02	0.36	6.68	5.35	4.01	4.22	9.57	8.24	ns
		–2	0.49	5.86	0.03	1.36	1.78	0.32	5.86	4.70	3.52	3.71	8.40	7.23	ns
100 µA	12 mA	Std.	0.66	5.67	0.04	1.83	2.38	0.43	5.67	4.36	5.06	5.59	9.07	7.75	ns
		–1	0.56	4.82	0.04	1.55	2.02	0.36	4.82	3.71	4.31	4.75	7.71	6.59	ns
		–2	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79	ns
100 µA	16 mA	Std.	0.66	5.35	0.04	1.83	2.38	0.43	5.35	3.96	5.15	5.76	8.75	7.35	ns
		–1	0.56	4.55	0.04	1.55	2.02	0.36	4.55	3.36	4.38	4.90	7.44	6.25	ns
		–2	0.49	4.00	0.03	1.36	1.78	0.32	4.00	2.95	3.85	4.30	6.53	5.49	ns
100 µA	24 mA	Std.	0.66	4.96	0.04	1.83	2.38	0.43	4.96	3.27	5.23	6.38	8.35	6.67	ns
		–1	0.56	4.22	0.04	1.55	2.02	0.36	4.22	2.78	4.45	5.43	7.11	5.67	ns
		–2	0.49	3.70	0.03	1.36	1.78	0.32	3.70	2.44	3.91	4.76	6.24	4.98	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to* *Table 2-6 on page 2-5* *for derating values.*

***Table 2-40* • 1.8 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	15.84	0.04	1.45	1.91	0.43	15.65	15.84	2.78	1.58	17.89	18.07	ns
	–1	0.56	13.47	0.04	1.23	1.62	0.36	13.31	13.47	2.37	1.35	15.22	15.37	ns
	–2	0.49	11.83	0.03	1.08	1.42	0.32	11.69	11.83	2.08	1.18	13.36	13.50	ns
4 mA	Std.	0.66	11.39	0.04	1.45	1.91	0.43	11.60	10.76	3.26	2.77	13.84	12.99	ns
	–1	0.56	9.69	0.04	1.23	1.62	0.36	9.87	9.15	2.77	2.36	11.77	11.05	ns
	–2	0.49	8.51	0.03	1.08	1.42	0.32	8.66	8.03	2.43	2.07	10.33	9.70	ns
6 mA	Std.	0.66	8.97	0.04	1.45	1.91	0.43	9.14	8.10	3.57	3.36	11.37	10.33	ns
	–1	0.56	7.63	0.04	1.23	1.62	0.36	7.77	6.89	3.04	2.86	9.67	8.79	ns
	–2	0.49	6.70	0.03	1.08	1.42	0.32	6.82	6.05	2.66	2.51	8.49	7.72	ns
8 mA	Std.	0.66	8.35	0.04	1.45	1.91	0.43	8.50	7.59	3.64	3.52	10.74	9.82	ns
	–1	0.56	7.10	0.04	1.23	1.62	0.36	7.23	6.45	3.10	3.00	9.14	8.35	ns
	–2	0.49	6.24	0.03	1.08	1.42	0.32	6.35	5.66	2.72	2.63	8.02	7.33	ns
12 mA	Std.	0.66	7.94	0.04	1.45	1.91	0.43	8.09	7.56	3.74	4.11	10.32	9.80	ns
	–1	0.56	6.75	0.04	1.23	1.62	0.36	6.88	6.43	3.18	3.49	8.78	8.33	ns
	–2	0.49	5.93	0.03	1.08	1.42	0.32	6.04	5.65	2.79	3.07	7.71	7.32	ns
16 mA	Std.	0.66	7.94	0.04	1.45	1.91	0.43	8.09	7.56	3.74	4.11	10.32	9.80	ns
	–1	0.56	6.75	0.04	1.23	1.62	0.36	6.88	6.43	3.18	3.49	8.78	8.33	ns
	–2	0.49	5.93	0.03	1.08	1.42	0.32	6.04	5.65	2.79	3.07	7.71	7.32	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

SSTL2 Class II

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

***Table 2-69* • Minimum and Maximum DC Input and Output Levels**

SSTL2 Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	μA[2]	μA[2]
18 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

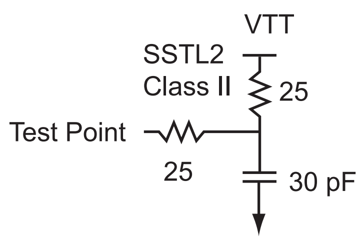


***Figure 2-19* • AC Loading**

***Table 2-70* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.25	1.25	1.25	30

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

***Table 2-71* • SSTL 2 Class II**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	0.66	2.17	0.04	1.33	0.43	2.21	1.77			4.44	ns
–1	0.56	0.56	1.84	0.04	1.14	0.36	1.88	1.51			3.78	ns
–2	0.49	0.49	1.62	0.03	1.00	0.32	1.65	1.32			3.32	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

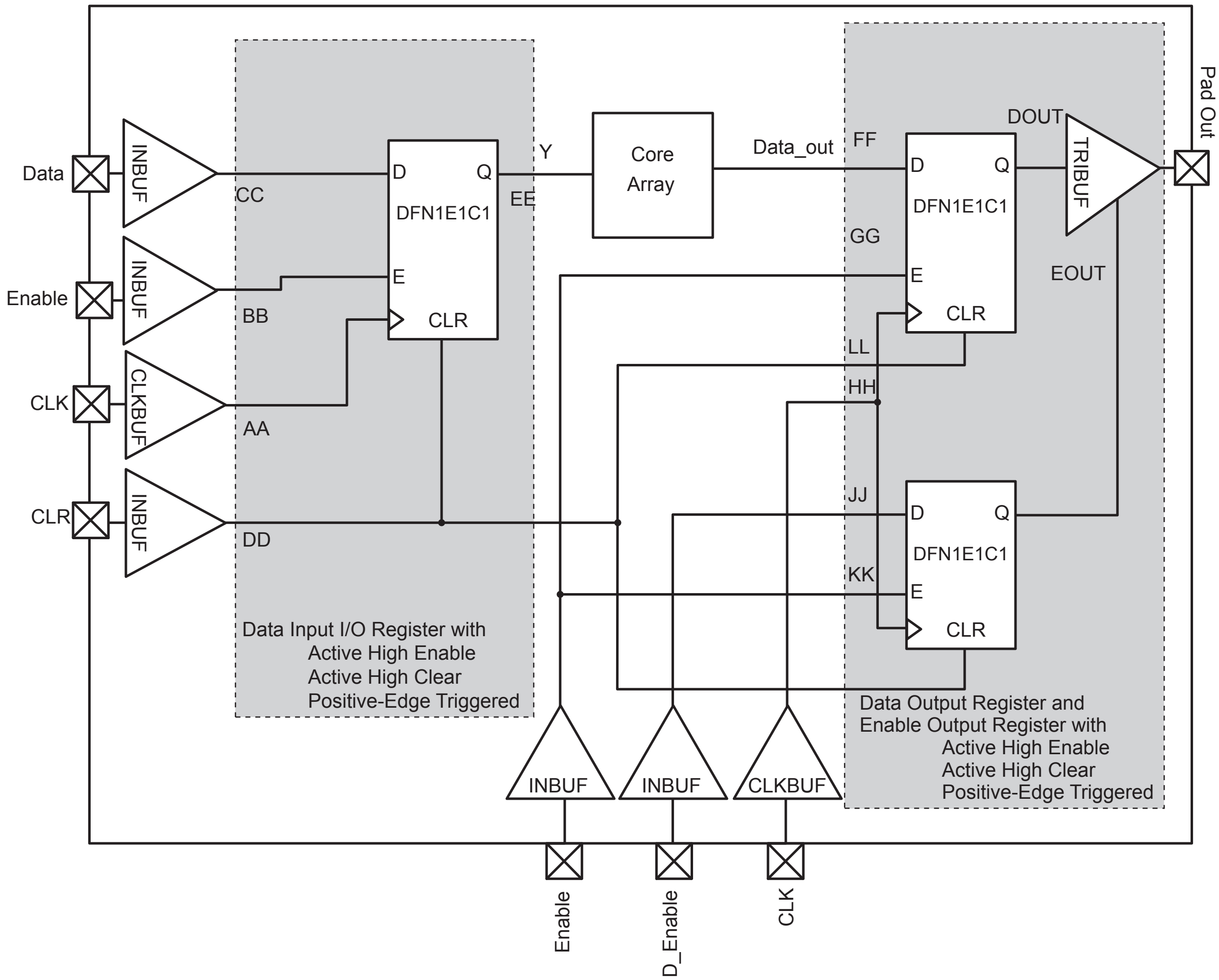


Figure 2-26 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

Table 2-85 • **Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-26 on page 2-55 for more information.

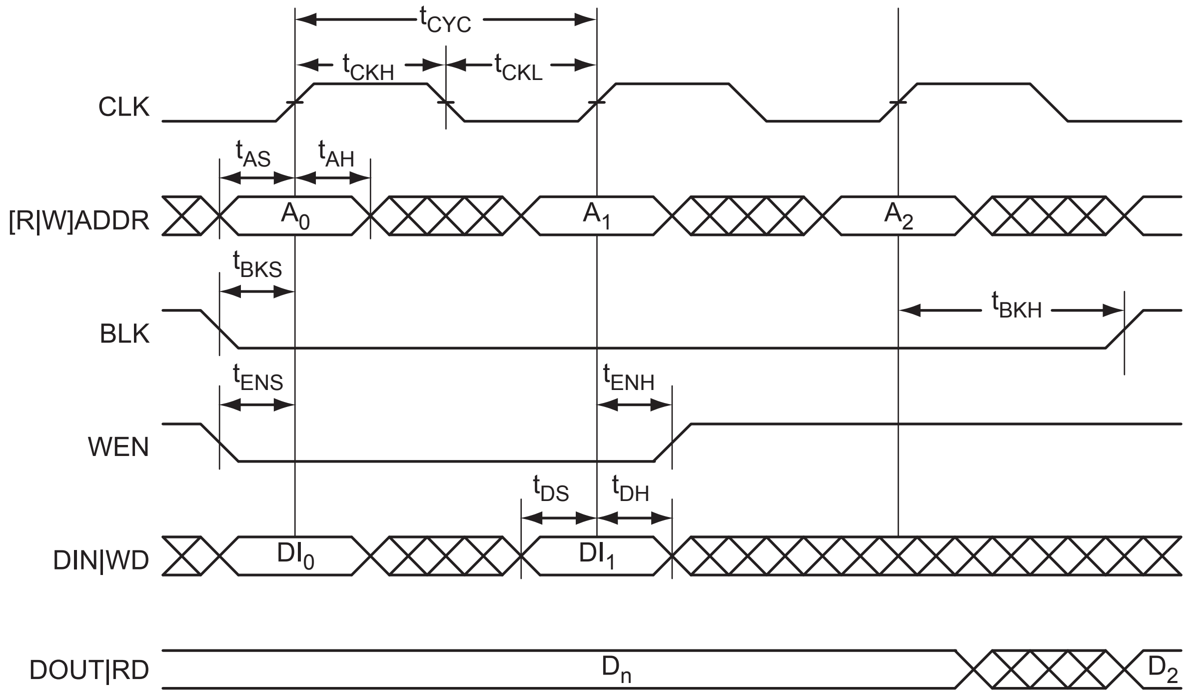


Figure 2-43 • **RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**

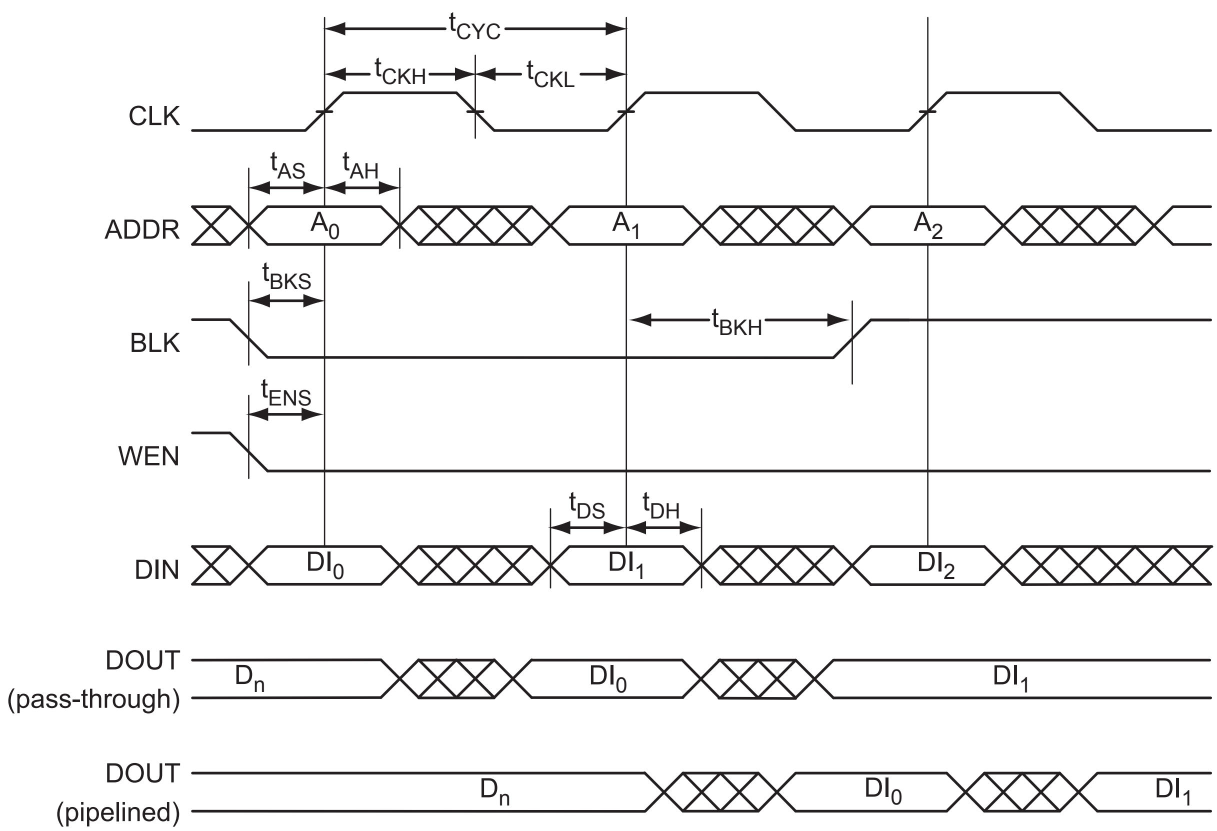


Figure 2-44 • **RAM Write, Output as Write Data. Applicable to RAM4K9 Only.**

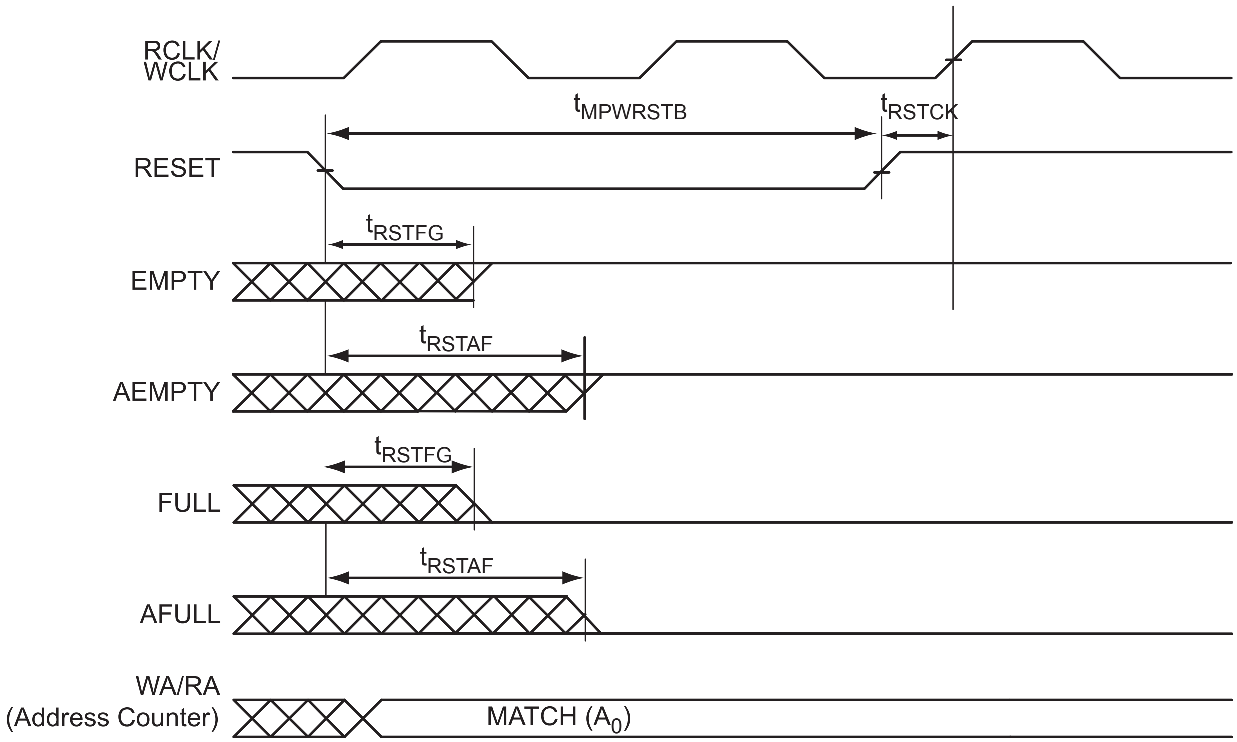


Figure 2-49 • **FIFO Reset**

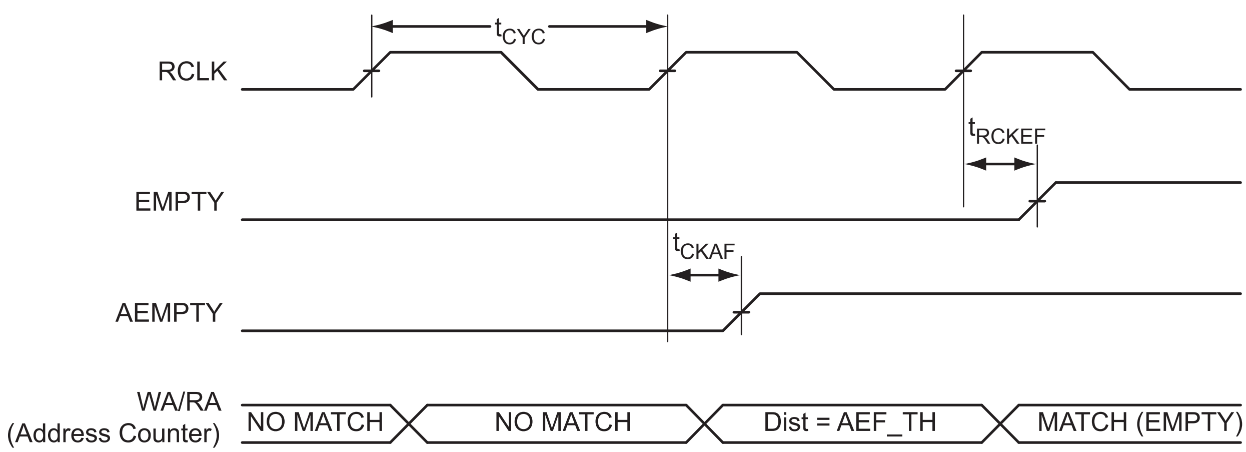
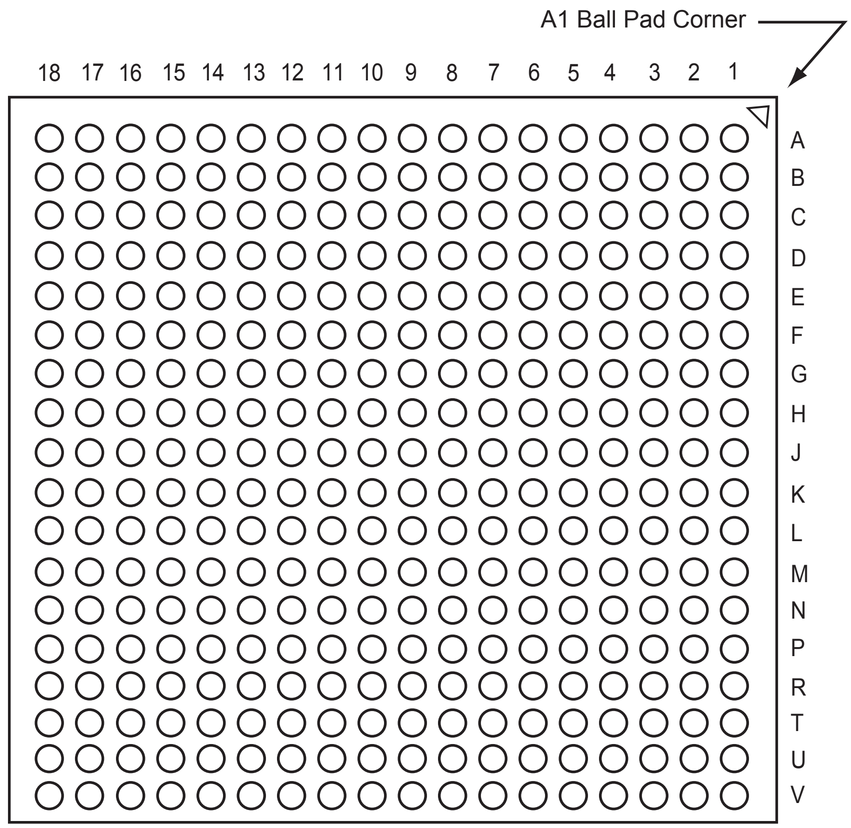


Figure 2-50 • **FIFO EMPTY Flag and AEMPTY Flag Assertion**

PQ208	
Pin Number	A3PE3000 Function
118	IO134NDB3V2
119	IO134PDB3V2
120	IO132NDB3V2
121	IO132PDB3V2
122	GND
123	VCCIB3
124	GCC2/IO117PSB3V0
125	GCB2/IO116PSB3V0
126	NC
127	IO115NDB3V0
128	GCA2/IO115PDB3V0
129	GCA1/IO114PPB3V0
130	GND
131	VCCPLC
132	GCA0/IO114NPB3V0
133	VCOMPLC
134	GCB0/IO113NDB2V3
135	GCB1/IO113PDB2V3
136	GCC1/IO112PSB2V3
137	IO110NDB2V3
138	IO110PDB2V3
139	IO106PSB2V3
140	VCCIB2
141	GND
142	VCC
143	IO99NDB2V2
144	IO99PDB2V2
145	IO96NDB2V1
146	IO96PDB2V1
147	IO91NDB2V1
148	IO91PDB2V1
149	IO88NDB2V0
150	IO88PDB2V0
151	GBC2/IO84PSB2V0
152	GBA2/IO82PSB2V0
153	GBB2/IO83PSB2V0
154	VMV2
155	GNDQ
156	GND
157	VMV1
158	GNDQ
159	GBA1/IO81PDB1V4
160	GBA0/IO81NDB1V4
161	GBB1/IO80PDB1V4
162	GND
163	GBB0/IO80NDB1V4
164	GBC1/IO79PDB1V4
165	GBC0/IO79NDB1V4
166	IO74PDB1V4
167	IO74NDB1V4
168	IO70PDB1V3
169	IO70NDB1V3
170	VCCIB1
171	VCC
172	IO56PSB1V1
173	IO55PDB1V1
174	IO55NDB1V1
175	IO54PDB1V1
176	IO54NDB1V1
177	IO40PDB0V4
178	GND
179	IO40NDB0V4
180	IO37PDB0V4
181	IO37NDB0V4
182	IO35PDB0V4
183	IO35NDB0V4
184	IO32PDB0V3
185	IO32NDB0V3
186	VCCIB0
187	VCC
188	IO28PDB0V3
189	IO28NDB0V3
190	IO24PDB0V2
191	IO24NDB0V2
192	IO21PSB0V2
193	IO16PDB0V1
194	IO16NDB0V1
195	GND
196	IO11PDB0V1
197	IO11NDB0V1
198	IO08PDB0V0
199	IO08NDB0V0
200	VCCIB0
201	GAC1/IO02PDB0V0
202	GAC0/IO02NDB0V0
203	GAB1/IO01PDB0V0
204	GAB0/IO01NDB0V0
205	GAA1/IO00PDB0V0
206	GAA0/IO00NDB0V0
207	GNDQ
208	VMV0

FG324



Note: This is the bottom view of the package.

Note

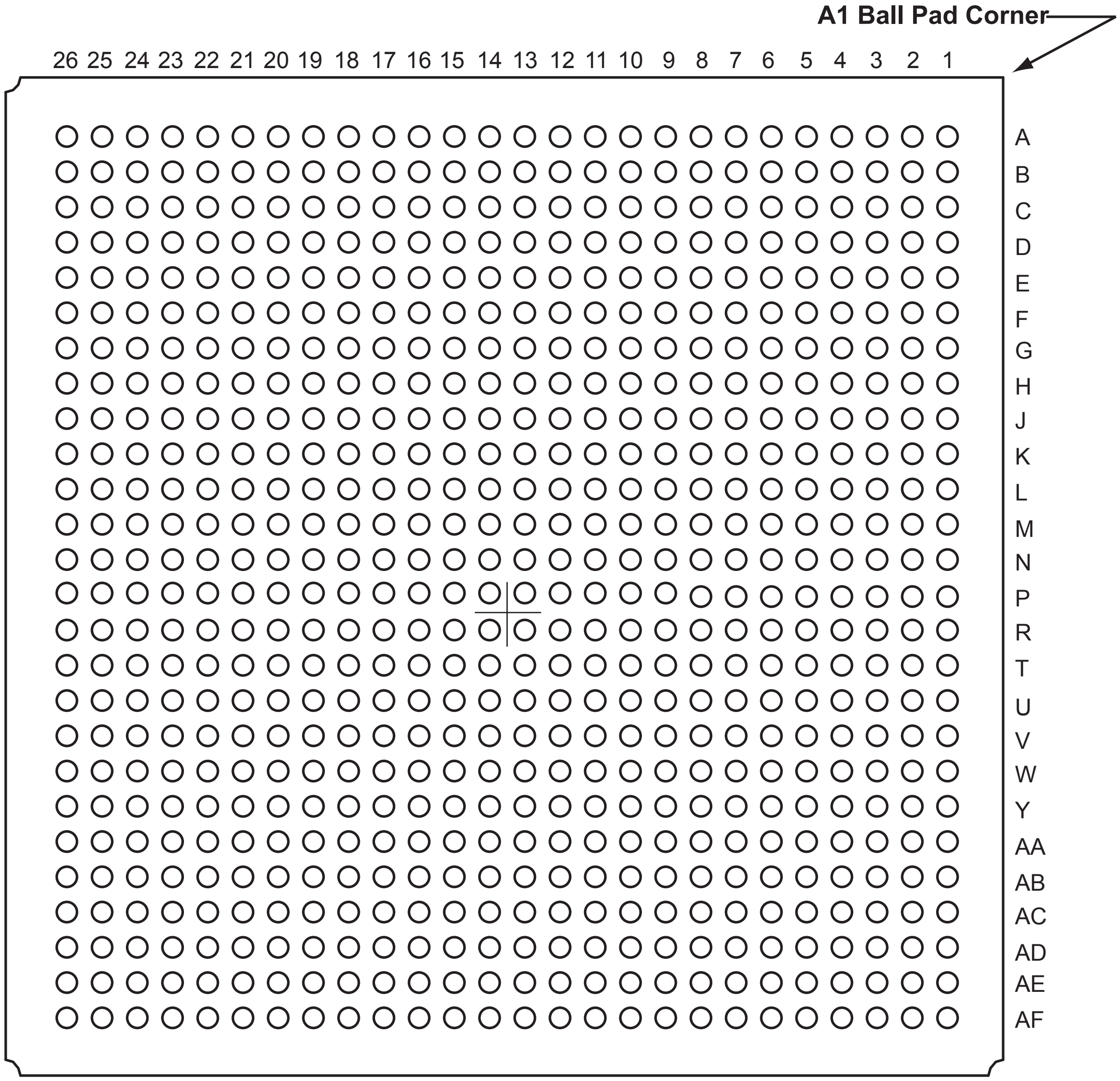
For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	A3PE1500 Function
H19	IO67PDB2V1
H20	VCC
H21	VMV2
H22	IO74PSB2V2
J1	IO212NDB7V2
J2	IO212PDB7V2
J3	VMV7
J4	IO206PDB7V1
J5	IO204PDB7V1
J6	IO210PDB7V2
J7	IO215NDB7V3
J8	VCCIB7
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB2
J16	IO60NDB2V0
J17	IO65NDB2V1
J18	IO65PDB2V1
J19	IO75PPB2V2
J20	GNDQ
J21	IO77PDB2V2
J22	IO79PDB2V3
K1	IO200NDB7V1
K2	IO200PDB7V1
K3	GNDQ
K4	IO206NDB7V1
K5	IO204NDB7V1
K6	IO210NDB7V2
K7	GFC1/IO192PPB7V0
K8	VCCIB7
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB2
K16	GCC1/IO85PPB2V3
K17	IO73NDB2V2
K18	IO73PDB2V2
K19	IO81NPB2V3
K20	IO75NPB2V2
K21	IO77NDB2V2
K22	IO79NDB2V3
L1	NC
L2	IO196PDB7V0
L3	IO196NDB7V0
L4	GFB0/IO191NPB7V0
L5	GFA0/IO190NDB6V2
L6	GFB1/IO191PPB7V0
L7	VCOMPLF
L8	GFC0/IO192NPB7V0
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO85NPB2V3
L16	GCB1/IO86PPB2V3
L17	GCA0/IO87NPB3V0
L18	VCOMPLC
L19	GCB0/IO86NPB2V3
L20	IO81PPB2V3
L21	IO83NDB2V3
L22	IO83PDB2V3
M1	GNDQ
M2	IO185NPB6V2
M3	IO189NDB6V2
M4	GFA2/IO189PDB6V2
M5	GFA1/IO190PDB6V2
M6	VCCPLF
M7	IO188NDB6V2
M8	GFB2/IO188PDB6V2
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO89PPB3V0
M16	GCA1/IO87PPB3V0
M17	GCC2/IO90PPB3V0
M18	VCCPLC
M19	GCA2/IO88PDB3V0
M20	IO88NDB3V0
M21	IO93PDB3V0
M22	NC
N1	IO185PPB6V2
N2	IO183NDB6V2
N3	VMV6
N4	GFC2/IO187PPB6V2
N5	IO184PPB6V2
N6	IO186PDB6V2
N7	IO186NDB6V2
N8	VCCIB6
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB3
N16	IO89NPB3V0

FG484	
Pin Number	A3PE3000 Function
V15	IO155NDB4V0
V16	GDB2/IO155PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	IO146PDB3V4
V22	IO142NDB3V3
W1	IO239NDB6V0
W2	IO237PDB6V0
W3	IO230PSB5V4
W4	GND
W5	IO232NDB5V4
W6	GEB2/IO232PDB5V4
W7	IO231NDB5V4
W8	IO214NDB5V2
W9	IO214PDB5V2
W10	IO200NDB5V0
W11	IO192NDB4V4
W12	IO184NDB4V3
W13	IO184PDB4V3
W14	IO156NDB4V0
W15	GDC2/IO156PDB4V0
W16	IO154NDB4V0
W17	GDA2/IO154PDB4V0
W18	TMS
W19	GND
W20	IO150NDB3V4
W21	IO146NDB3V4
W22	IO148PPB3V4
Y1	VCCIB6
Y2	IO237NDB6V0
Y3	IO228NDB5V4
Y4	IO224NDB5V3
Y5	GND
Y6	IO220NDB5V3

FG484	
Pin Number	A3PE3000 Function
Y7	IO220PDB5V3
Y8	VCC
Y9	VCC
Y10	IO200PDB5V0
Y11	IO192PDB4V4
Y12	IO188NPB4V4
Y13	IO187PSB4V4
Y14	VCC
Y15	VCC
Y16	IO164NDB4V1
Y17	IO164PDB4V1
Y18	GND
Y19	IO158PPB4V0
Y20	IO150PDB3V4
Y21	IO148NPB3V4
Y22	VCCIB3

FG676



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG676	
Pin Number	A3PE1500 Function
C9	IO10PDB0V1
C10	IO16PDB0V2
C11	IO20PDB0V2
C12	IO24PDB0V3
C13	IO23PDB0V2
C14	IO28PDB0V3
C15	IO31PDB0V3
C16	IO32NDB1V0
C17	IO36NDB1V0
C18	IO37NDB1V0
C19	IO45NDB1V1
C20	IO42PPB1V1
C21	IO46NPB1V1
C22	IO48NPB1V2
C23	GBB0/IO56NPB1V3
C24	VMV1
C25	GBC2/IO60PDB2V0
C26	IO60NDB2V0
D1	IO218NDB7V3
D2	IO218PDB7V3
D3	GND
D4	VMV7
D5	IO221NDB7V3
D6	GAC0/IO02NDB0V0
D7	GAC1/IO02PDB0V0
D8	IO05NDB0V0
D9	IO08PDB0V1
D10	IO12NDB0V1
D11	IO18NDB0V2
D12	IO17NDB0V2
D13	IO25NDB0V3
D14	IO29NDB0V3
D15	IO33NDB1V0
D16	IO40PDB1V1
D17	IO43NDB1V1
D18	IO47PDB1V1

FG676	
Pin Number	A3PE1500 Function
D19	IO45PDB1V1
D20	IO46PPB1V1
D21	IO48PPB1V2
D22	GBA0/IO57NPB1V3
D23	GNDQ
D24	GBB1/IO56PPB1V3
D25	GBB2/IO59PDB2V0
D26	IO59NDB2V0
E1	IO212PDB7V2
E2	IO211NDB7V2
E3	IO211PDB7V2
E4	IO220NPB7V3
E5	GNDQ
E6	GAB2/IO220PPB7V3
E7	GAB1/IO01PDB0V0
E8	IO05PDB0V0
E9	IO08NDB0V1
E10	IO12PDB0V1
E11	IO18PDB0V2
E12	IO17PDB0V2
E13	IO25PDB0V3
E14	IO29PDB0V3
E15	IO33PDB1V0
E16	IO40NDB1V1
E17	IO43PDB1V1
E18	IO47NDB1V1
E19	IO54NDB1V3
E20	IO52NDB1V2
E21	IO52PDB1V2
E22	VCCPLB
E23	GBA1/IO57PPB1V3
E24	IO63PDB2V0
E25	IO63NDB2V0
E26	IO68PDB2V1
F1	IO212NDB7V2
F2	IO203PPB7V1

FG676	
Pin Number	A3PE1500 Function
F3	IO213NDB7V2
F4	IO213PDB7V2
F5	GND
F6	VCCPLA
F7	GAB0/IO01NDB0V0
F8	GNDQ
F9	IO03PDB0V0
F10	IO13PDB0V1
F11	IO15PDB0V1
F12	IO19PDB0V2
F13	IO21PDB0V2
F14	IO27NDB0V3
F15	IO35PDB1V0
F16	IO39NDB1V0
F17	IO51PDB1V2
F18	IO53PDB1V2
F19	IO54PDB1V3
F20	VMV2
F21	VCOMPLB
F22	IO61PDB2V0
F23	IO61NDB2V0
F24	IO66PDB2V1
F25	IO66NDB2V1
F26	IO68NDB2V1
G1	IO203NPB7V1
G2	IO207NDB7V2
G3	IO207PDB7V2
G4	IO216NDB7V3
G5	IO216PDB7V3
G6	VCOMPLA
G7	VMV0
G8	VCC
G9	IO03NDB0V0
G10	IO13NDB0V1
G11	IO15NDB0V1
G12	IO19NDB0V2

FG896	
Pin Number	A3PE3000 Function
T11	VCC
T12	GND
T13	GND
T14	GND
T15	GND
T16	GND
T17	GND
T18	GND
T19	GND
T20	VCC
T21	VCCIB3
T22	IO109NPB2V3
T23	IO116NDB3V0
T24	IO118NDB3V0
T25	IO122NPB3V1
T26	GCA1/IO114PPB3V0
T27	GCB0/IO113NPB2V3
T28	GCA2/IO115PPB3V0
T29	VCCPLC
T30	IO121PDB3V0
U1	IO268PDB6V4
U2	IO264NDB6V3
U3	IO264PDB6V3
U4	IO258PDB6V3
U5	IO258NDB6V3
U6	IO257PPB6V2
U7	IO261PPB6V3
U8	IO265NDB6V3
U9	IO263NDB6V3
U10	VCCIB6
U11	VCC
U12	GND
U13	GND
U14	GND
U15	GND
U16	GND

FG896	
Pin Number	A3PE3000 Function
U17	GND
U18	GND
U19	GND
U20	VCC
U21	VCCIB3
U22	IO120PDB3V0
U23	IO128PDB3V1
U24	IO124PDB3V1
U25	IO124NDB3V1
U26	IO126PDB3V1
U27	IO129PDB3V1
U28	IO127PDB3V1
U29	IO125PDB3V1
U30	IO121NDB3V0
V1	IO268NDB6V4
V2	IO262PDB6V3
V3	IO260PDB6V3
V4	IO252PDB6V2
V5	IO257NPB6V2
V6	IO261NPB6V3
V7	IO255PDB6V2
V8	IO259PDB6V3
V9	IO259NDB6V3
V10	VCCIB6
V11	VCC
V12	GND
V13	GND
V14	GND
V15	GND
V16	GND
V17	GND
V18	GND
V19	GND
V20	VCC
V21	VCCIB3
V22	IO120NDB3V0

FG896	
Pin Number	A3PE3000 Function
V23	IO128NDB3V1
V24	IO132PDB3V2
V25	IO130PPB3V2
V26	IO126NDB3V1
V27	IO129NDB3V1
V28	IO127NDB3V1
V29	IO125NDB3V1
V30	IO123PDB3V1
W1	IO266NDB6V4
W2	IO262NDB6V3
W3	IO260NDB6V3
W4	IO252NDB6V2
W5	IO251NDB6V2
W6	IO251PDB6V2
W7	IO255NDB6V2
W8	IO249PPB6V1
W9	IO253PDB6V2
W10	VCCIB6
W11	VCC
W12	GND
W13	GND
W14	GND
W15	GND
W16	GND
W17	GND
W18	GND
W19	GND
W20	VCC
W21	VCCIB3
W22	IO134PDB3V2
W23	IO138PDB3V3
W24	IO132NDB3V2
W25	IO136NPB3V2
W26	IO130NPB3V2
W27	IO141PDB3V3
W28	IO135PDB3V2

Revision	Changes	Page
v2.0 (continued)	Table 3-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	3-5
	Table 3-5 • Package Thermal Resistivities was updated.	3-5
	Table 3-10 • Different Components Contributing to the Dynamic Power Consumption in ProASIC3E Devices was updated.	3-8
	t_{WRO} and t_{CCKH} were added to Table 3-94 • RAM4K9 and Table 3-95 • RAM512X18.	3-74 to 3-74
	The note in Table 3-24 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-23
	Figure 3-43 • Write Access After Write onto Same Address, Figure 3-44 • Read Access After Write onto Same Address, and Figure 3-45 • Write Access After Read onto Same Address are new.	3-71 to 3-73
	Figure 3-53 • Timing Diagram was updated.	3-80
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3PE1500 "208-Pin PQFP" table is new.	4-4
	The A3PE1500 "484-Pin FBGA" table is new.	4-18
	The A3PE1500 "A3PE1500 Function" table is new.	4-24
Advance v0.6 (January 2007)	In the "Packaging Tables" table, the number of I/Os for the A3PE1500 was changed for the FG484 and FG676 packages.	ii
Advance v0.5 (April 2006)	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-8 • Very-Long-Line Resources was updated.	2-8
	The footnotes in Figure 2-27 • CCC/PLL Macro were updated.	2-28
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21
	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-8 • Very-Long-Line Resources was updated.	2-8
	The footnotes in Figure 2-27 • CCC/PLL Macro were updated.	2-28
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21
	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25